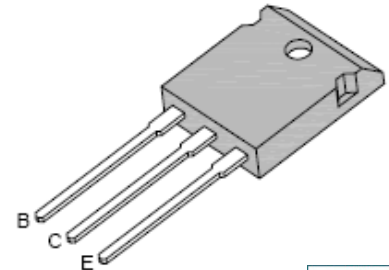


Power Transistor (PNP)

Features

- 2SB817E transistor is designed for use in general purpose power amplifier, application



TO-3P



Mechanical Data

Case:	TO-3P, Plastic Package
Terminals:	Plated leads solderable per MIL-STD-750, Method 2026
Weight:	0.22 ounce, 6.2 gram

Maximum Ratings ($T_{Ambient}=25^{\circ}\text{C}$ unless noted otherwise)

Symbol	Description	2SB817E	Unit	Conditions
V_{CB0}	Collector-Base Voltage	160	V	
V_{CEO}	Collector-Emitter Voltage	140	V	
V_{EB0}	Emitter-Base Voltage	6.0	V	
I_C	Collector Current-Continuous	12	A	
I_{CM}	Collector Current-Peak	15	A	
P_{tot}	Power Dissipation at $T_C=25^{\circ}\text{C}$	100	W	
	Power Dissipation Derate above 25°C	0.8	W/ $^{\circ}\text{C}$	
R_{θJC}	Thermal Resistance from Junction to Case	1.25	$^{\circ}\text{C}/\text{W}$	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^{\circ}\text{C}$	

Power Transistor (PNP)

2SB817E

Electrical Characteristics ($T_{Ambient}=25^{\circ}\text{C}$ unless noted otherwise)

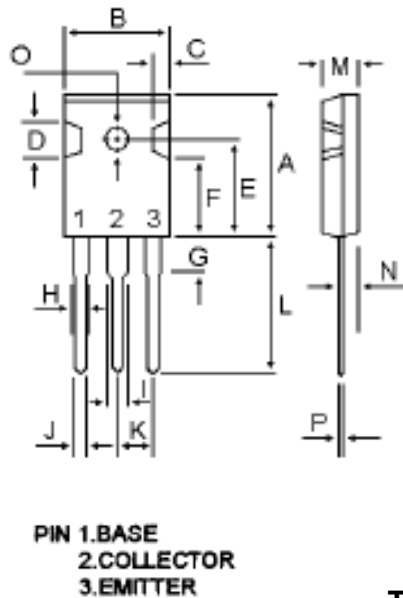
Symbol	Description	2SB817E		Unit	Conditions
		Min.	Max.		
*h_{FE}	D.C. Current Gain	100	200		V _{CE} =5.0V, I _C =1.0A
		20	-		V _{CE} =5.0V, I _C =6.0A
V_{(BR)CBO}	Collector-Base Breakdown Voltage	160	-	V	I _C =5.0mA, I _E =0
V_{(BR)CEO}	Collector-Emitter Breakdown Voltage	140	-	V	I _C =5.0mA, I _B =0
V_{(BR)EBO}	Emitter-Base Breakdown Voltage	6.0	-	V	I _B =5.0mA, I _C =0
*V_{CE(sat)}	Collector-Emitter Saturation Voltage	-	2.5	V	I _C =5.0A, I _B =0.5A
*V_{BE(on)}	Base-Emitter On Voltage	-	1.5	V	I _C =1.0A, V _{CE} =5.0V
I_{CBO}	Collector-Base Cut-off Current	-	100	μA	V _{CB} =80V, I _E =0
I_{EBO}	Emitter-Base Cut-off Current	-	100	μA	V _{EB} =4.0V, I _C =0
t_{on}	Turn-on Time	-	0.3	μS	V _{CC} =20V, I _C =1.0A I _{B1} =-I _{B2} =100mA PW=20μS
t_s	Storage Time	-	7.0	μS	
t_f	Fall Time		0.7	μS	

*Pulse Test: Pulse Width= 300μs, Duty Cycle ≤2.0%

Power Transistor (PNP)

2SB817E

Dimensions in mm



DIM	MILLIMETERS	
	MIN	MAX
A	20.63	22.38
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.81	15.22
F	11.72	12.84
G	4.20	4.50
H	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.26	5.66
L	18.50	21.50
M	4.68	5.36
N	2.40	2.80
O	3.25	3.65
P	0.55	0.70

TO-3P

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